

ABSTRACT

The present invention provides a silicon epitaxial wafer having an excellent IG capability all over the radial direction thereof and a process for manufacturing the same. The present invention is directed to a silicon epitaxial wafer having an excellent gettering capability all over the radial direction thereof, wherein density of oxide precipitates detectable in the interior of a silicon single crystal substrate after epitaxial growth is $1 \times 10^9/\text{cm}^3$ or higher at any position in the radial direction.